

Photocouplers Infrared LED & Photo IC

TLP350,TLP350F

1. Applications

- · Industrial Inverters
- · Air Conditioner Inverters
- · MOSFET Gate Drivers
- · IGBT Gate Drivers
- Induction Cooktop and Home Appliances

2. General

The TLP350 is a photocoupler in a DIP8 package that consists of a infrared light-emitting diode (LED) optically coupled to an integrated high-gain, high-speed photodetector IC chip. It provides guaranteed performance and specifications at temperatures up to $100\,^{\circ}$ C. The TLP350 has an internal Faraday shield that provides a guaranteed Common-mode transient immunity of $\pm 15\,$ kV/ μ s. It has a totem-pole output that can both sink and source current. The TLP350 is ideal for IGBT of small capacity to middle capacity and power MOSFET gate drive.

3. Features

- (1) Buffer logic type (totem pole output)
- (2) Output peak current: ±2.5 A (max)
- (3) Operating temperature: -40 to 100 °C
- (4) Supply current: 2.0 mA (max)
- (5) Supply voltage: 15 to 30 V
- (6) Threshold input current: 5 mA (max)
- (7) Propagation delay time: 500 ns (max)
- (8) Common-mode transient immunity: ±15 kV/μs (min)
- (9) Isolation voltage: 3750 Vrms (min)
- (10) Safety standards

UL-recognized: UL 1577, File No.E67349

cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349

VDE-approved: EN IEC 60747-5-5 (Note 1)

CQC-approved: GB4943.1 Japan Factory

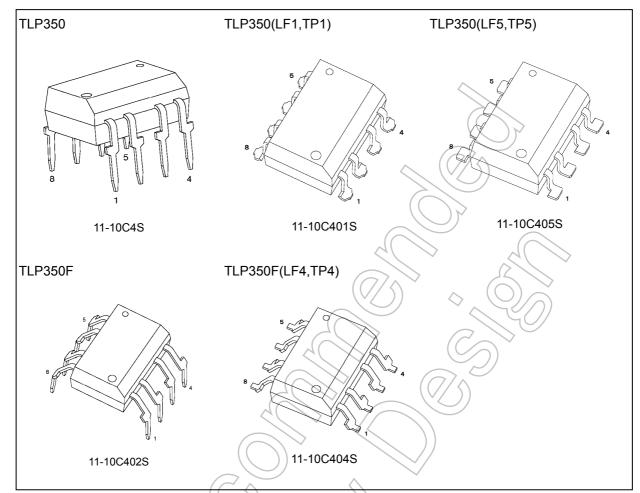
Note 1: When an EN IEC 60747-5-5 approved type is needed, please designate the Option (D4).



Start of commercial production

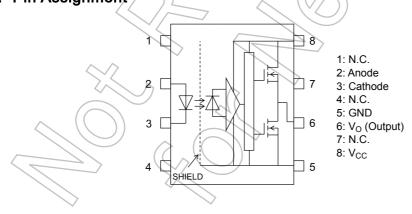


4. Packaging (Note)



Note: Through-hole type: TLP350, TLP350F Lead forming option: (LF1), (LF4), (LF5) Taping option: (TP1), (TP4), (TP5)

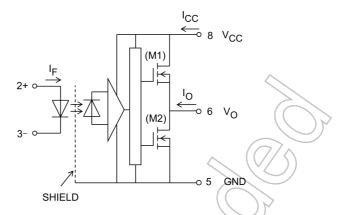
5. Pin Assignment



Rev.2.0



6. Internal Circuit (Note)



Note: A 0.1- μ F bypass capacitor must be connected between pin 8 and pin 5.

7. Principle of Operation

7.1. Truth Table

Input	LED	M1	M2	Output
Н	ON	ON	OFF	H
L	OFF	OFF	ON	

7.2. Mechanical Parameters

Characteristics	7.62 mm Pitch TLP350	10.16 mm Pitch TLP350F	Unit
Creepage distances	7.0 (min)	8.0 (min)	mm
Clearance distances	7.0 (min)	8.0 (min)	
Internal isolation thickness	0.4 (min)	0.4 (min)	



8. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteris	stics	Symbol	Note	Rating	Unit
LED	Input forward current		I _F		20	mA
	Input forward current derating	(T _a ≥ 85 °C)	$\Delta I_F/\Delta T_a$		-0.54	mA/°C
	Peak transient input forward current	t	I _{FPT}	(Note 1)	1	Α
	Peak transient input forward current derating	t (T _a ≥ 85 °C)	$\Delta I_{FPT}/\Delta T_a$		-25	mA/°C
	Input reverse voltage		V_R) 7 5	V
	Input power dissipation		P_D		40	mW
	Input power dissipation derating	(T _a ≥ 85 °C)	$\Delta P_D/\Delta T_a$	$(\vee /)$	-1.0	mW/°C
	Junction temperature		Tj		125	°C
Detector	Peak high-level output current	(T _a = -40 to 100 °C)	I _{OPH}	(Note 2)	-2.5	Α
	Peak low-level output current	(T _a = -40 to 100 °C)	TORL	(Note 2)	+2.5	
	Output voltage		V_0	>	35	٧
	Supply voltage	(T _a < 95 °C)	Aec		35	
	Supply voltage derating	(T _a ≥ 95 °C)	$\Delta V_{CC}/\Delta T_a$		-1.0	V/°C
	Output power dissipation) Po	\Diamond	260	mW
	Output power dissipation derating	(T _a ≥ 110 °C)	$\Delta P_{O}/\Delta T_{a}$		-6.5	mW/°C
	Junction temperature		Tj		125	°C
Common	Operating frequency		f	(Note 3)	50	kHz
	Operating temperature		Topr		-40 to 100	ů
	Storage temperature		T _{stg}	(/))	-55 to 125	
	Lead soldering temperature	(10 s)	T _{sol}	(Note 4)	260	
	Isolation voltage	(AC, 60 s, R.H. ≤ 60 %)	BV _S	(Note 5)	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note: A ceramic capacitor (0.1 μF) should be connected between pin 8 and pin 5 to stabilize the operation of a high-gain linear amplifier. Otherwise, this photocoupler may not switch properly. The bypass capacitor should be placed within 1 cm of each pin.

Note 1: Pulse width $(P_W) \le 1 \mu s$, 300 pps

Note 2: Exponential waveform. Pulse width $\leq 0.3~\mu s$, f $\leq 15~kHz$

Note 3: If the rising slope of the supply voltage (V_{CC}) for the detector is steep, stable operation of the internal circuits cannot be guaranteed.

Be sure to set 3.0 V/ μs or less for a rising slope of the V_{CC}.

Note 4: ≥ 2 mm below seating plane.

Note 5: This device is considered as a two-terminal device: Pins 1, 2, 3 and 4 are shorted together, and pins 5, 6, 7 and 8 are shorted together.



9. Recommended Operating Conditions (Note)

Characteristics	Symbol	Note	Min	Тур.	Max	Unit
Input on-state current	I _{F(ON)}	(Note 1)	7.5	_	10	mA
Input off-state voltage	$V_{F(OFF)}$		0	_	0.8	V
Supply voltage	V _{CC}	(Note 2)	15	_	30	
Peak high-level output current	I _{OPH}	(Note 3)	7	_	-2.0	Α
Peak low-level output current	I _{OPL}	(Note 3)		7	+2.0	
Operating temperature	T _{opr}		-40	ガー	100	°C

Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this data sheet should also be considered.

Note 1: The rise and fall times of the input on-current should be less than 0.5 μs .

Note 2: Denotes the operating range, not the recommended operating condition.

Note 3: Exponential waveform. $I_{OPH} \ge -2.0 \text{ A} \ (\le 0.3 \ \mu\text{s}), \ I_{OPL} \le 2.0 \ A \ (\le 0.3 \ \mu\text{s}), \ T_a = 100 \ ^{\circ}\text{C}$

10. Electrical Characteristics (Note) (Unless otherwise specified, T_a = -40 to 100 °C)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Input forward voltage	V _F		_	I _F = 10 mA, T _a = 25 °C		1.55	1.8	V
Input forward voltage temperature coefficient	$\Delta V_F/\Delta T_a$		_	U _E = 10 mA		-2.4	_	mV/°C
Input reverse current	I_{R}		4	$V_R = 5 \text{ V}, T_a = 25 ^{\circ}\text{C}$)) —	_	10	μА
Input capacitance	Ct		/(-)/	$V = 0 V, f = 1 MHz, T_a = 25 °C$	/ _	45	250	pF
Peak high-level output current	I _{OPH}	(Note 1)	Fig. 13.1.1	V _{CC} = 30 V, I _F = 5 mA, V ₈₋₆ = 3.5 V	_	-2.5	-1.0	А
			<u>)</u>	V _{CC} = 15 V, I _F = 5 mA, V ₈₋₆ = 7.0 V	_	_	-2.0	
Peak low-level output current	I _{OPL} ((Note 1)	Fig. 13.1.2	$V_{CC} = 30 \text{ V, I}_{F} = 0 \text{ mA,}$ $V_{6-5} = 2.5 \text{ V}$	1.0	2.5	_	
				$V_{CC} = 15 \text{ V, I}_{F} = 0 \text{ mA,}$ $V_{6-5} = 7.0 \text{ V}$	2.0	_	_	
High-level output voltage	V _{OH}		Fig. 13.1.3	$V_{CC1} = +15 \text{ V},$ $V_{EE1} = -15 \text{ V},$ $R_L = 200 \Omega, I_F = 5 \text{ mA}$	11.0	13.9	_	V
Low-level output voltage	V _{OL}		Fig. 13.1.4	V_{CC1} = +15 V, V_{EE1} = -15 V, R_L = 200 Ω , V_F = 0.8 V	_	-14.9	-12.5	
High-level supply current	I _{CCH}	$\langle \rangle$	Fig. 13.1.5	V_{CC} = 30 V, I _F = 10 mA, V _O = Open	_	1.5	2.0	mA
Low-level supply current	I _{CCL}		Fig. 13.1.6	V_{CC} = 30 V, I_F = 0 mA, V_O = Open	_	1.5	2.0	
Threshold input current (L/H)	IFLH)	_	$V_{CC} = 15 \text{ V}, V_{O} > 1 \text{ V},$ $I_{O} = 0 \text{ mA}$	_	1.2	5	
Threshold input voltage (H/L)	VFHL		_	V _{CC} = 15 V, V _O < 1 V, I _O = 0 mA	0.8	_	_	V
Supply voltage	V _{CC}				15	_	30	V
UVLO threshold voltage	V _{UVLO} +		Fig. 13.1.9	$I_F = 5 \text{ mA}, V_O > 2.5 \text{ V}$	11.0	12.5	13.5	
	V _{UVLO} -		Fig. 13.1.9	$I_F = 5 \text{ mA}, V_O < 2.5 \text{ V}$	9.5	11.0	12.0	
UVLO hysteresis	UVLO _{HYS}		Fig. 13.1.9		_	1.5	_	

Note: All typical values are at T_a = 25 °C. Note 1: I_O application time \leq 50 μ s; single pulse.



11. Isolation Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Note Test Conditions		Min	Тур.	Max	Unit
Total capacitance (input to output)	Cs	(Note 1)	V _S = 0 V, f = 1 MHz	_	1.0		pF
Isolation resistance	R _S	(Note 1)	V_{S} = 500 V, R.H. \leq 60 %	1 × 10 ¹²	1014		Ω
Isolation voltage	BVS	(Note 1)	AC, 60 s	3750			Vrms

Note 1: This device is considered as a two-terminal device: Pins 1, 2, 3 and 4 are shorted together, and pins 5, 6, 7 and 8 are shorted together.

12. Switching Characteristics (Note) (Unless otherwise specified, Ta = -40 to 100 °C)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Propagation delay time (L/H)	t _{pLH}	(Note 1)		$\begin{aligned} I_F &= 0 \rightarrow 5 \text{ mA, V}_{CC} = 30 \text{ V,} \\ R_g &= 20 \ \Omega, \ C_g = 10 \text{ nF} \end{aligned}$	> 50	150	500	ns
Propagation delay time (H/L)	t _{pHL}	(Note 1)		$I_F = 5 \rightarrow 0$ mA, $V_{CC} = 30$ V, $R_g = 20 \Omega$, $C_g = 10$ nF	50	150	500	
Pulse width distortion	t _{pHL} -t _{pLH}	(Note 1)		$I_F = 0 \longleftrightarrow 5 \text{ mA}, V_{CC} = 30 \text{ V},$ $R_g = 20 \Omega, C_g = 10 \text{ nF}$	- (350	
Rise time	t _r	(Note 1)		$I_F = 0 \rightarrow 5 \text{ mA}, V_{CC} = 30 \text{ V},$ $R_g = 20 \Omega, C_g = 10 \text{ nF}$	-(15) –	
Fall time	t _f	(Note 1)		$I_F = 5 \rightarrow 0 \text{ mA}, V_{CC} = 30 \text{ V},$ $R_g = 20 \Omega, C_g = 10 \text{ nF}$	7	8	_	
High-level common-mode transient immunity	CM _H	(Note 2)	Fig. 13.1.8	$V_{CM} = 1000 V_{p-p}, I_F = 5 \text{ mA},$ $V_{CC} = 30 V, T_a = 25 ^{\circ}C,$ $V_{O(min)} = 26 V$	-15	_	_	kV/μs
Low-level common-mode transient immunity	CM _L	(Note 3)		$V_{CM} = 1000 \text{ V}_{0-p}, I_F = 0 \text{ mA},$ $V_{CC} = 30 \text{ V}, T_a = 25 \text{ °C},$ $V_{O(max)} = 1 \text{ V}$	15	_		

Note: All typical values are at $T_a = 25 \, ^{\circ}\text{C}$.

Note 1: f = 25 kHz, duty = 50 %, input current $t_r = t_f = 5$ ns, C_L is approximately 15 pF which includes probe and stray wiring capacitance.

Note 2: CM_H is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic high state ($V_O \ge 26 \text{ V}$).

Note 3: CM_L is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state ($V_0 < 1 \text{ V}$).





13. Test Circuits and Characteristics Curves

13.1. Test Circuits

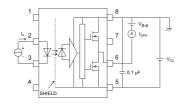


Fig. 13.1.1 I_{OPH} Test Circuit

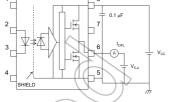


Fig. 13.1.2 JOPL Test Circuit

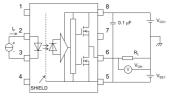


Fig. 13.1.3 V_{OH} Test Circuit

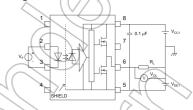


Fig. 13.1.4 VOL Test Circuit

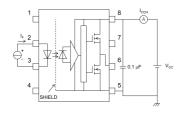


Fig. 13.1.5 I_{CCH} Test Circuit

* P.G.: Pulse Generator

 $I_F = 5 \text{ mA (P.G.*)}$

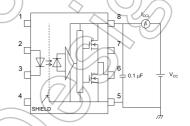
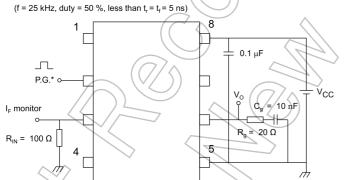


Fig. 13,1.6 I_{CCL} Test Circuit



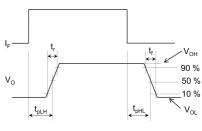
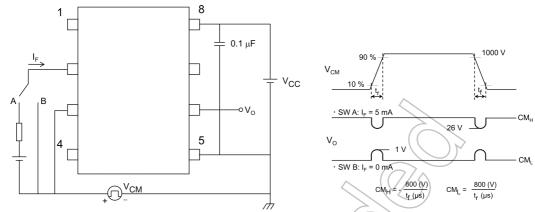


Fig. 13.1.7 Switching Time Test Circuit and Waveform

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 $\mathrm{CM_L}(\mathrm{CM_H})$ is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.

Fig. 13.1.8 Common-Mode Transient Immunity Test Circuit and Waveform

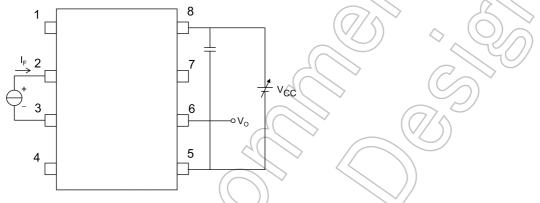
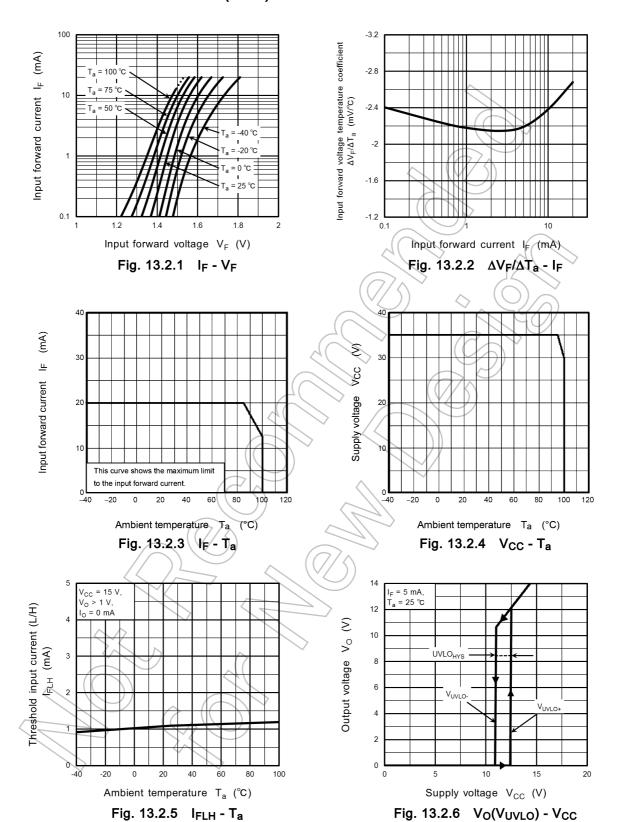


Fig. 13.1.9 V_{CC}-V_{O(VUVLO)} Test Circuit

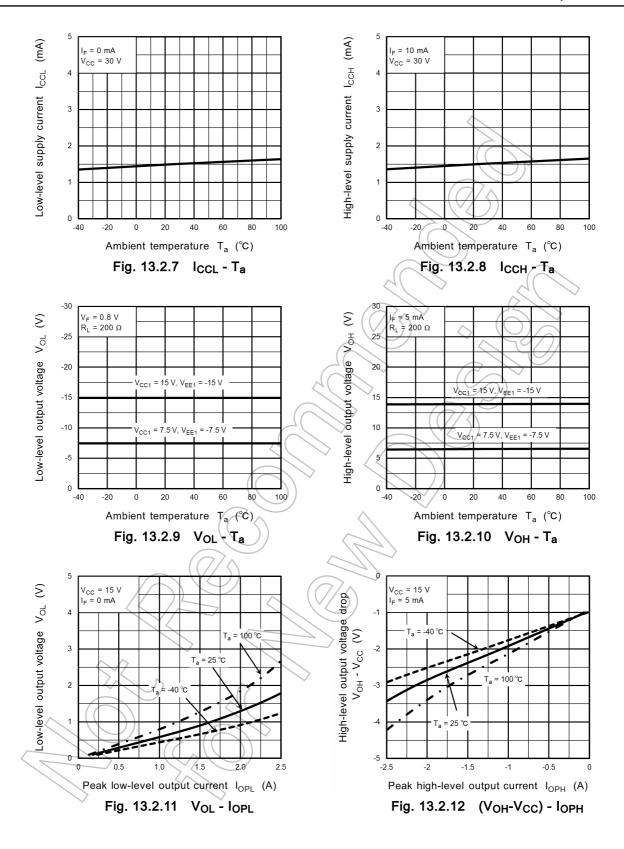




13.2. Characteristics Curves (Note)









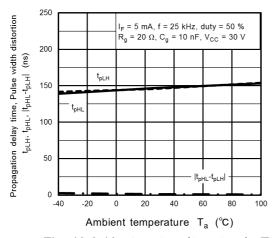


Fig. 13.2.13 $t_{pLH}, t_{pHL}, |t_{pHL}-t_{pLH}| - T_a$

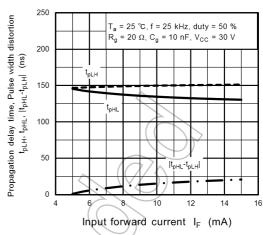


Fig. 13.2.14 $t_{pLH}, t_{pHL}, |t_{pHL}-t_{pLH}| - I_F$

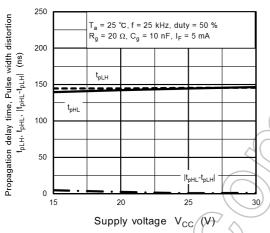


Fig. 13.2.15 t_{pLH} , t_{pHL} , t_{pHL} - t_{pLH} - V_{CC}

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.





14. Soldering and Storage

14.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

When using soldering reflow.

The soldering temperature profile is based on the package surface temperature. (See the figure shown below, which is based on the package surface temperature.) Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.

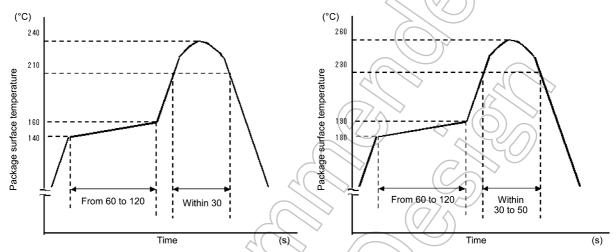


Fig. 14.1.1 An example of a temperature profile Fig. 14.1.2 An example of a temperature profile when Sn-Pb eutectic solder is used when lead(Pb)-free solder is used

- When using soldering flow (Applicable to both eutectic solder and Lead(Pb)-Free solder) Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds. Mounting condition of 260 °C within 10 seconds is recommended. Flow soldering must be performed once.
- When using soldering Iron

Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C

Heating by soldering iron must be done only once per lead.

14.2. Precautions for General Storage

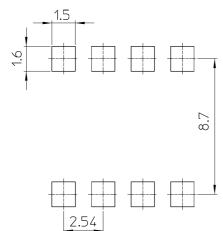
- Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the devices in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the devices in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.



15. Land Pattern Dimensions (for reference only)

Unit: mm

TLP350



TLP350F

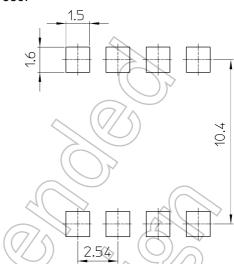


Fig. 15.1 Lead forming and taping option (LF1), (TP1), (LF5), (TP5)

Fig. 15.2 Lead forming and taping option (LF4), (TP4)

16. Marking (Note)

TLP350,TLP350F

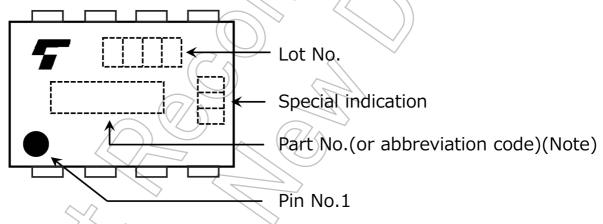
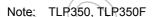


Fig. 16.1 Marking Example (Note)





17. EN IEC 60747-5-5 Option (D4) Specification

· Part number: TLP350, TLP350F (Note 1)

• The following part naming conventions are used for the devices that have been qualified according to option (D4) of EN IEC 60747.

Example: TLP350(D4-TP1,F)

D4: EN IEC 60747 option

TP1: Tape type

F: [[G]]/RoHS COMPATIBLE (Note 2)

Note 1: Use TOSHIBA standard type number for safety standard application e.g., TLP350(D4-TP1,F) \rightarrow TLP350

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Description		Symbol	Rating	Unit	
Application classification for rated mains voltage ≤ 300 Vrms for rated mains voltage ≤ 600 Vrms		7/s)	I-IV I-III		
Climatic classification			40 / 125 / 21	_	
Pollution degree			2	_	
Maximum and the first line of	TLPxxx type	\	890	Vacale	
Maximum operating insulation voltage	TLPxxxF type	VIORM	1140	Vpeak	
Input to output test voltage, Method A	TLPxxx type	W	1424	Vnook	
V_{pr} = 1.6 × V_{IORM} , type and sample test t_p = 10 s, partial discharge < 5 pC	TLPxxxF type	V _{pr}	1824	- Vpeak	
Input to output test voltage, Method B V _{pr} = 1.875 × V _{IORM} , 100 % production test	TLPxxx type	V	1670	Vpeak	
t _p = 1 s, partial discharge < 5 pC	TLPxxxF type	V _{pr}	2140	vpeak	
Highest permissible overvoltage (transient overvoltage, t _{pr} = 60 s)		VTR	8000	Vpeak	
Safety limiting values (max, permissible ratings in case of also refer to thermal derating current (input current I _F , P _{SO} = 0) power (output or total power dissipation) temperature		I _{si} P _{so} T _s	100 800 150	mA mW °C	
Insulation resistance V_{IO} = 500 V, T_a = 25 °C V_{IO} = 500 V, T_a = 100 °C V_{IO} = 500 V, T_a = T_s		R _{si}	$ \begin{array}{c} $	Ω	

Fig. 17.1 EN IEC 60747 Isolation Characteristics



		7.62 mm pitch TLPxxx type	10.16 mm pitch TLPxxxF type	
Minimum creepage distance	Cr	7.0 mm	8.0 mm	
Minimum clearance	CI	7.0 mm	8.0 mm	
Minimum insulation thickness	ti	0.4 mm		
Comparative tracking index	CTI	175		

Fig. 17.2 Insulation Related Specifications (Note)

Note: If a printed circuit is incorporated, the creepage distance and clearance may be reduced below this value. (e. g., at a standard distance between soldering eye centers of 7.5 mm). If this is not permissible, the user shall take suitable measures.

Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data: Maintenance of the safety data shall be ensured by means of protective circuits.



Fig. 17.3 Marking on Packing for EN IEC 60747

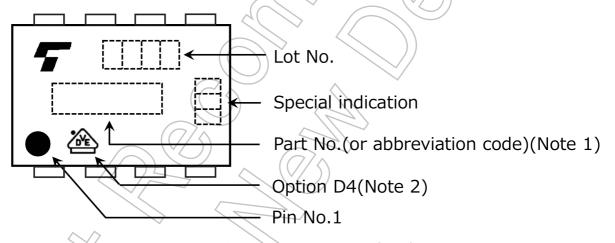
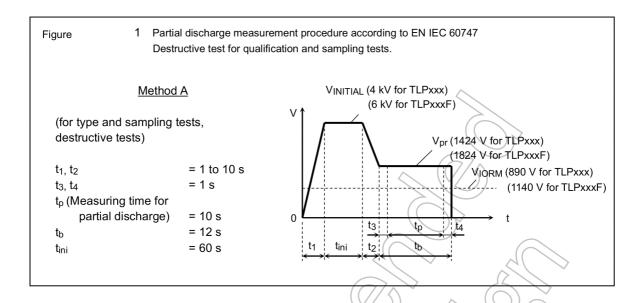


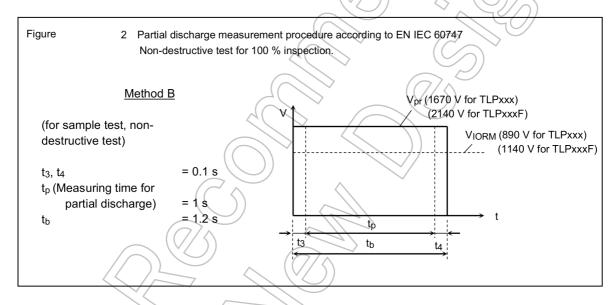
Fig. 17.4 Marking Example (Note)

Note 1: TLP350, TLP350F

Note 2: The above marking is applied to the photocouplers that have been qualified according to option (D4) of EN IEC 60747.







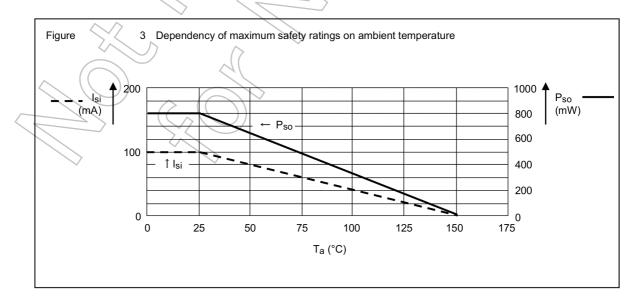
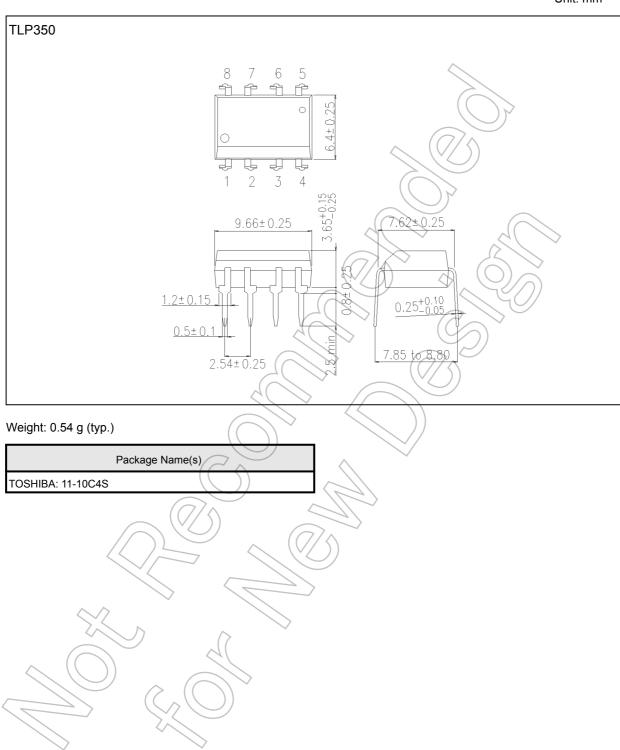
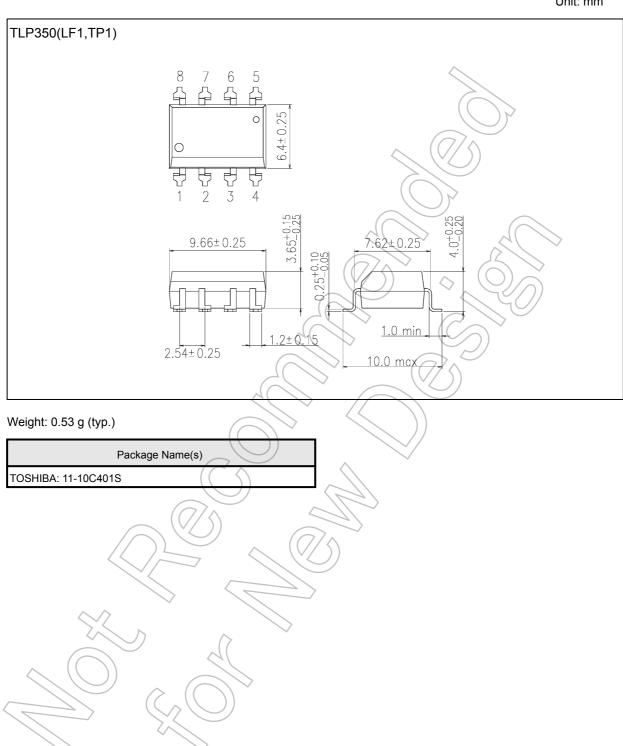


Fig. 17.5 Measurement Procedure



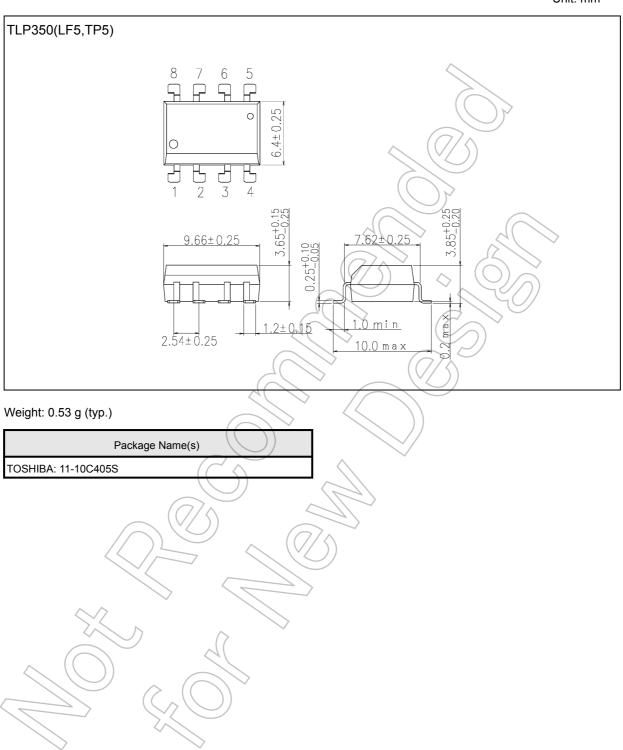






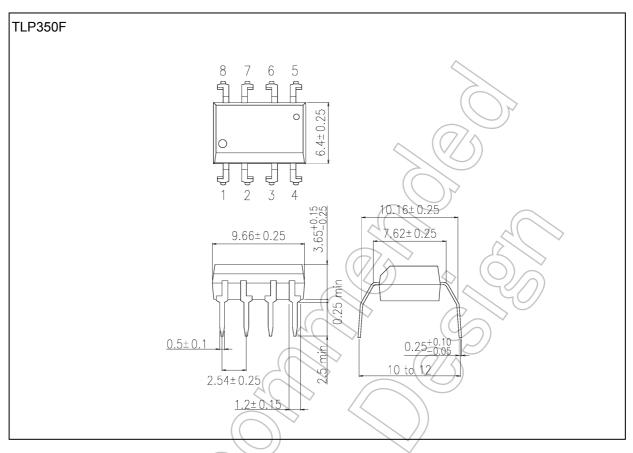


Unit: mm

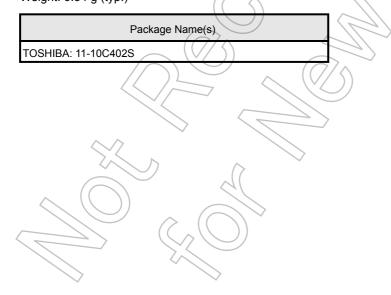


Rev.2.0

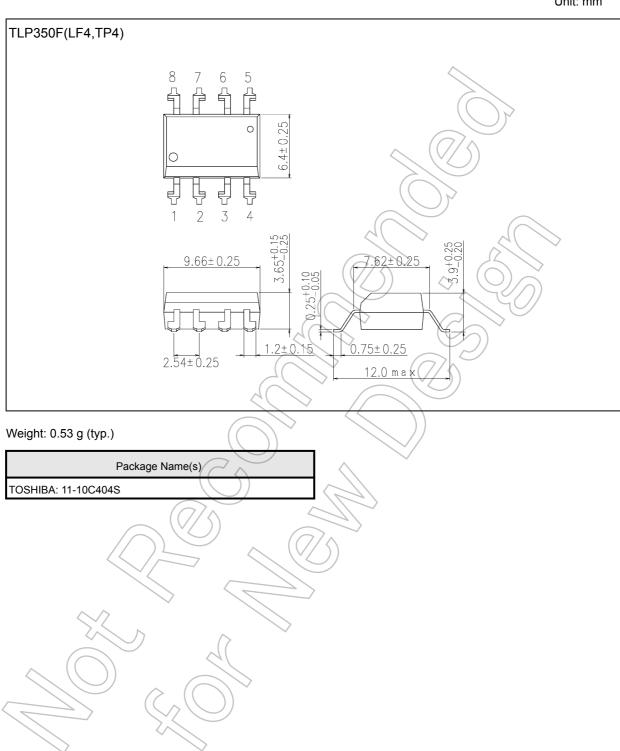














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